

SD5400 SERIES



N-Channel Lateral DMOS Quad FETs

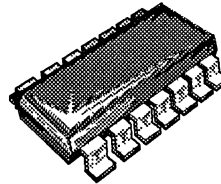
The Siliconix SD5400 series is a monolithic array of single-pole, single-throw analog switches designed for high-speed switching in audio, video and high frequency applications in communications, instrumentation, and process control. Designed with the Siliconix DMOS process, the SD5400 is rated for analog signals of ± 10 V, while the SD5401 and SD5402 are rated for ± 5 V and ± 7.5 V respectively.

These bidirectional switches feature very low interelectrode capacitance and on-resistance to achieve low insertion loss, crosstalk, and feedthrough performance. The threshold voltage for all switches is 2 V maximum, simplifying driver requirements for low level signal applications.

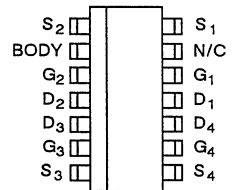
For additional design information please see performance curves DMCA, which are located in Section 7.

PART NUMBER	$V_{(BR)DS}$	$V_{GS(TH)}$	$r_{ds(ON)}$	t_{ON}
	MIN (V)	MAX (V)	MAX (Ω)	MAX (ns)
SD5400CY	20	2.0	70	2
SD5401CY	10	2.0	70	2
SD5402CY	15	2.0	70	2

SO-14



TOP VIEW



SIMILAR PRODUCTS

- TO-18, See SD211DE Series
- 16-Pin DIP, See SD5000 Series
- SOT-143, See SST211 Series
- Chips, Order SD540XCHP

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETERS/TEST CONDITIONS	SYMBOL	LIMIT			UNITS
		SD5400	SD5401	SD5402	
Gate-Source, Gate-Drain Voltage	V_{GS}, V_{GD}	30/-25	25/-15	30/-22.5	V
Drain-Substrate, Source-Substrate Voltage	V_{DB}, V_{SB}	25	15	22.5	
Drain-Source, Source-Drain Voltage	V_{DS}, V_{SD}	20	10	15	
Gate-Substrate Voltage ¹	V_{GB}	30/-0.3	25/-0.3	30/-0.3	
Drain Current	I_D	50			mA
Power Dissipation	Package	500			mW
	Each Device	300			
Power Derating (Package)		5			mW/ $^\circ\text{C}$
Operating Junction Temperature	T_J	-55 to 125			$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 125			
Lead Temperature (1/16" from case for 10 seconds)	T_L	300			

¹These devices feature an internal Zener protected gate.

ELECTRICAL CHARACTERISTICS ¹				LIMITS							
PARAMETER	SYMBOL	TEST CONDITIONS	TYP ²	SD5400CY		SD5401CY		SD5402CY		UNIT	
				MIN	MAX	MIN	MAX	MIN	MAX		
STATIC											
Drain-Source Breakdown Voltage	$V_{(BR)DS}$	$V_{GS} = V_{BS} = -5 \text{ V}$, $I_D = 10 \text{ nA}$	30	20		10		15		V	
Source-Drain Breakdown Voltage	$V_{(BR)SD}$	$V_{GD} = V_{BD} = -5 \text{ V}$, $I_S = 10 \text{ nA}$	22	20		10		15			
Drain-Substrate Breakdown Voltage	$V_{(BR)DB}$	$V_{GB} = 0 \text{ V}$ $I_D = 10 \text{ nA}$ Source OPEN	35	25		15		22.5			
Source-Substrate Breakdown Voltage	$V_{(BR)SB}$	$V_{GB} = 0 \text{ V}$ $I_S = 10 \mu\text{A}$ Drain OPEN	35	25		15		22.5			
Drain-Source Leakage	$I_{DS(OFF)}$	$V_{GS} = V_{BS} = -5 \text{ V}$	$V_{DS} = 20 \text{ V}$	0.9		10				nA	
			$V_{DS} = 10 \text{ V}$	0.4			10				
			$V_{DS} = 15 \text{ V}$	0.7				10			
Source-Drain Leakage	$I_{SD(OFF)}$	$V_{GD} = V_{BD} = -5 \text{ V}$	$V_{SD} = 20 \text{ V}$	1		10					
			$V_{SD} = 10 \text{ V}$	0.5			10				
			$V_{SD} = 15 \text{ V}$	0.8				10			
Gate Leakage	I_{GBS}	$V_{DB} = V_{SB} = 0 \text{ V}$, $V_{GB} = 30 \text{ V}$	10^{-5}		1		1		1	μA	
Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS} = V_{GS(th)}$, $I_S = 1 \mu\text{A}$ $V_{SB} = 0 \text{ V}$	0.7	0.1	2	0.1	2	0.1	2	V	
Drain-Source On-Resistance	$r_{DS(ON)}$	$I_D = 1 \text{ mA}$ $V_{SB} = 0 \text{ V}$	$V_{GS} = 5 \text{ V}$	58		70		70		70	Ω
			$V_{GS} = 10 \text{ V}$	38							
			$V_{GS} = 15 \text{ V}$	30							
			$V_{GS} = 20 \text{ V}$	26							
Resistance Match		$I_D = 1 \text{ mA}$, $V_{SB} = 0 \text{ V}$ $V_{GS} = 5 \text{ V}$	1		5		5		5		
DYNAMIC											
Forward Transconductance	g_{fs}	$V_{DS} = 10 \text{ V}$, $V_{SB} = 0 \text{ V}$ $I_D = 20 \text{ mA}$, $f = 1 \text{ kHz}$	11	10		10		10		mS	
Gate Node Capacitance	$C_{(GS+GD+GB)}$	$V_{DS} = 10 \text{ V}$, $f = 1 \text{ MHz}$ $V_{GS} = V_{BS} = -15 \text{ V}$	2.5		3.5		3.5		3.5	pF	
Drain Node Capacitance	$C_{(GD+DB)}$		1.1		2		2		2		
Source Node Capacitance	$C_{(GS+SB)}$		3.7		6		6		6		
Reverse Transfer Capacitance	C_{rss}		0.2		0.5		0.5		0.5		
Crosstalk			$f = 3 \text{ kHz}$, See Test Circuits in DMCA Performance Curves	-107							
SWITCHING											
Turn-ON Time	$t_{d(ON)}$	$V_{DD} = 5 \text{ V}$, $R_L = 680 \Omega$ $V_{IN} = 5 \text{ V}$	0.5		1		1		1	ns	
	t_r		0.6		1		1		1		
Turn-OFF Time	$t_{d(OFF)}$		2								
	t_f		6								

NOTES: 1. $T_A = 25^\circ\text{C}$ unless otherwise noted.

2. For design aid only, not subject to production testing.